

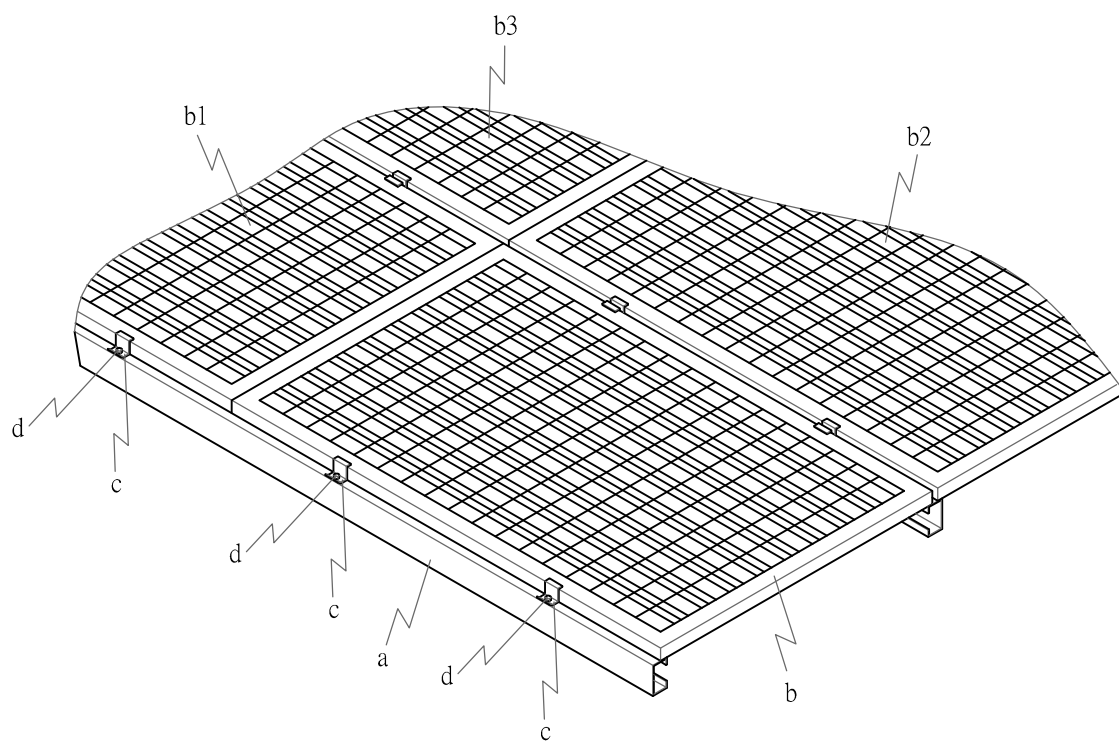


FIG 1

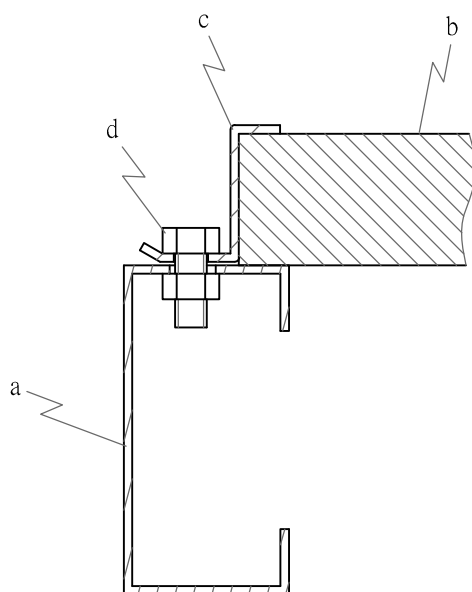


FIG 2

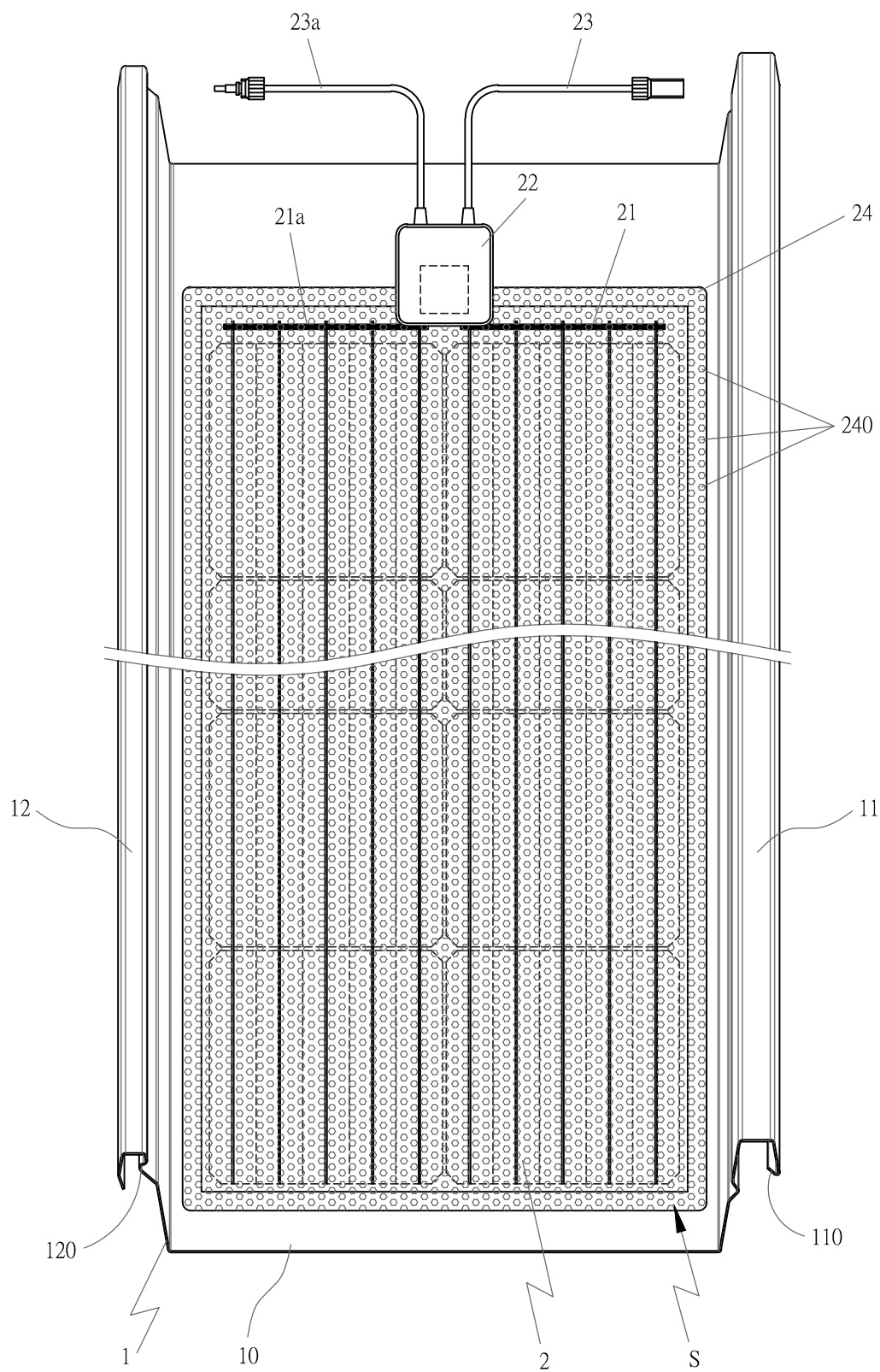


FIG 3

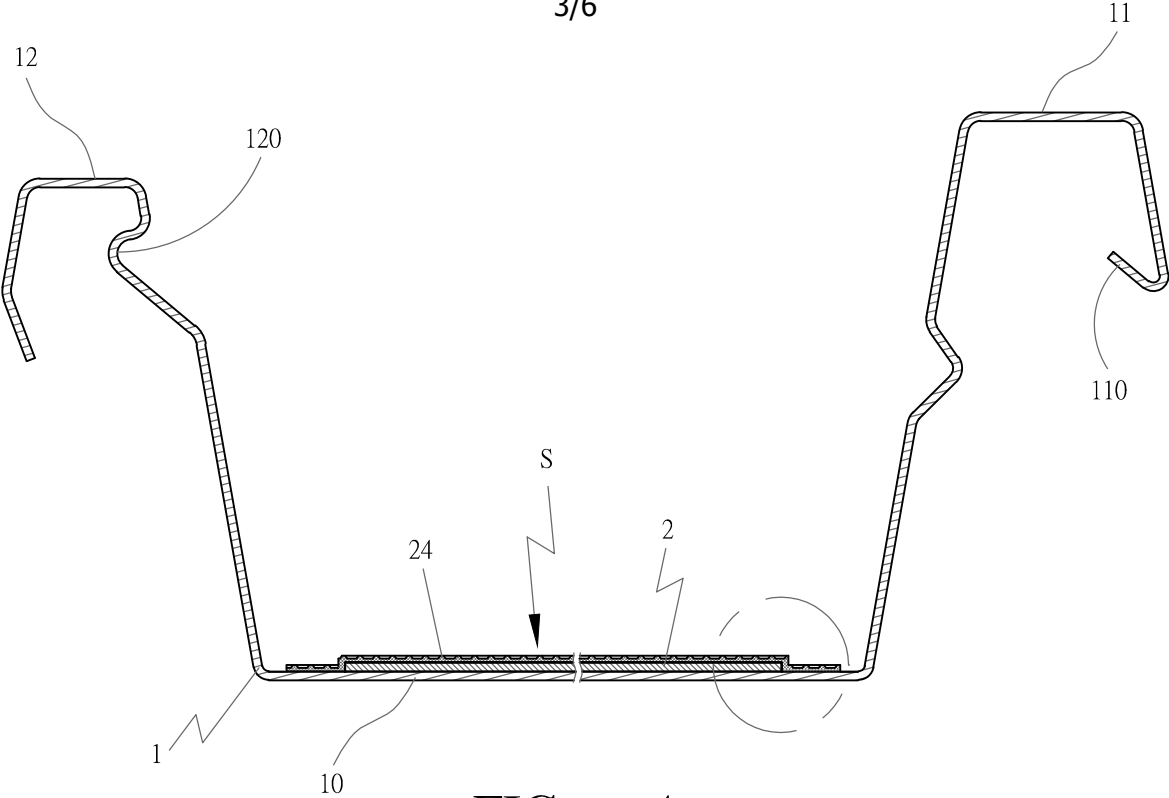


FIG 4

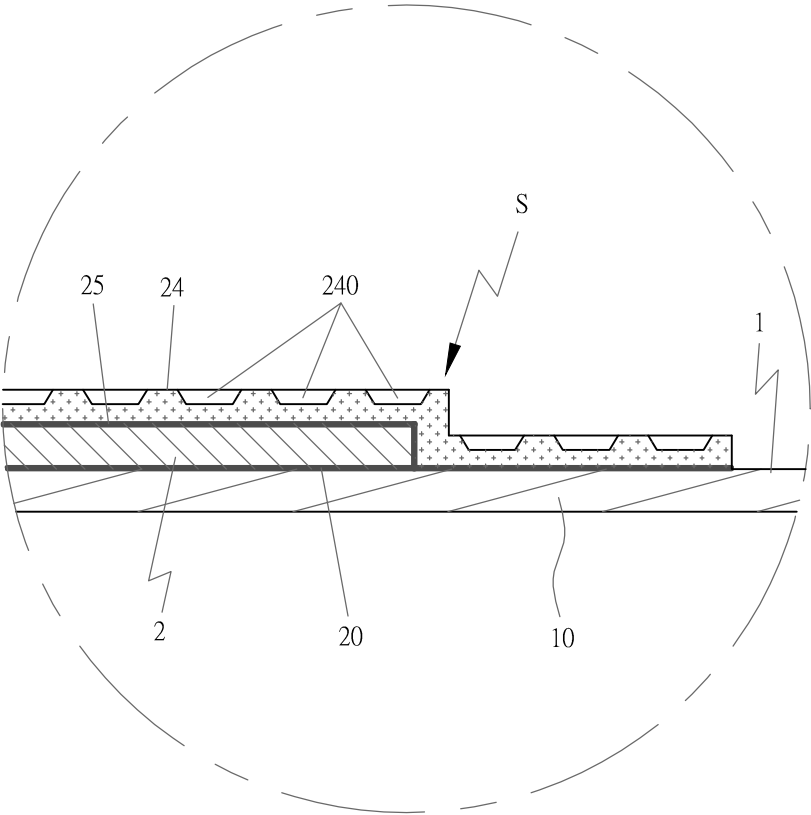


FIG 4A

The figure consists of two side-by-side cross-sectional diagrams of a semiconductor device. Both diagrams show a substrate labeled '10'. On top of the substrate is a thin layer labeled '2'. In the center of each diagram is a rectangular feature labeled '22' sitting on a base labeled '24'. To the left of this central feature is a structure labeled '12' which has a small protrusion at its top edge. To the right of the central feature is a larger, more complex structure labeled '11'. An arrow labeled 'S' points downwards towards the substrate between the central feature and the structures '12' and '11'. The left diagram shows a specific profile for the structures '12' and '11', while the right diagram shows an alternative profile for them.

FIG 6A

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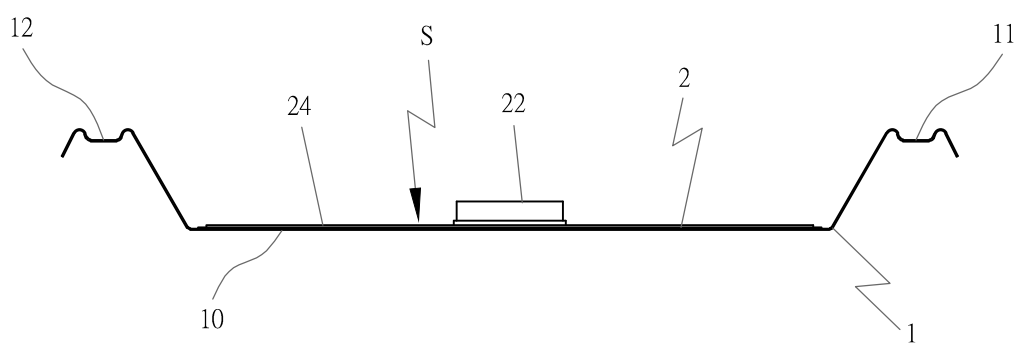


FIG 7

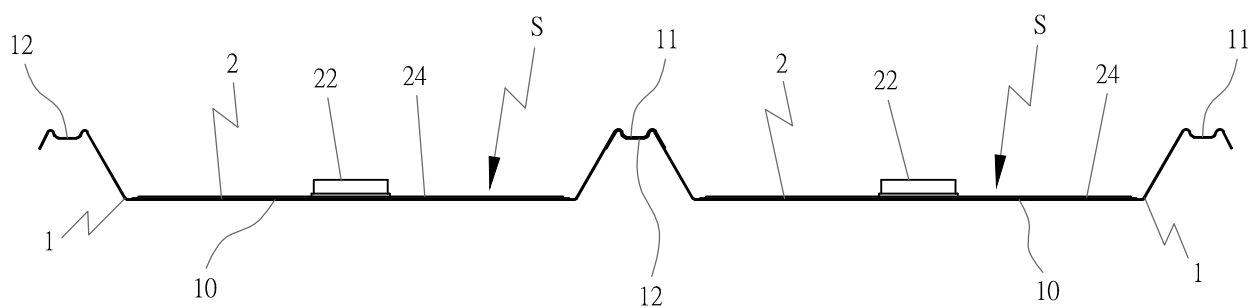


FIG 7A

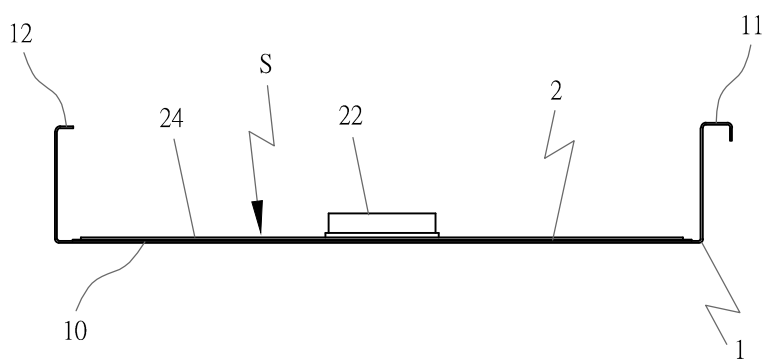


FIG 8

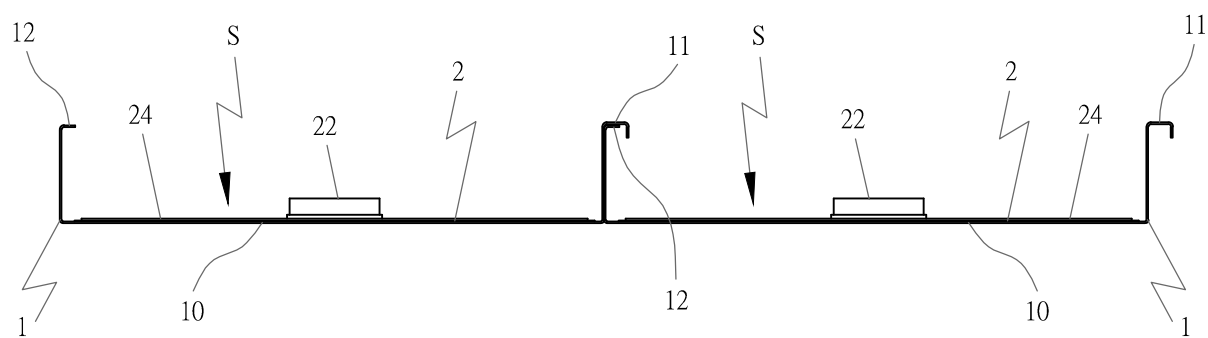


FIG 8A

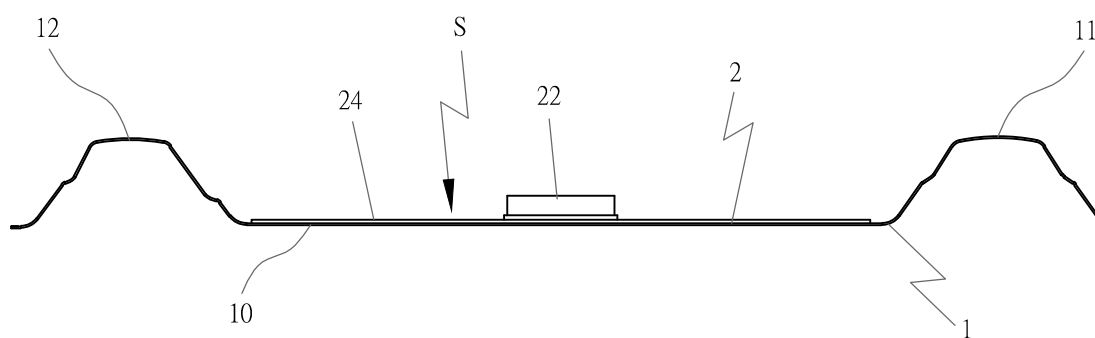


FIG 9

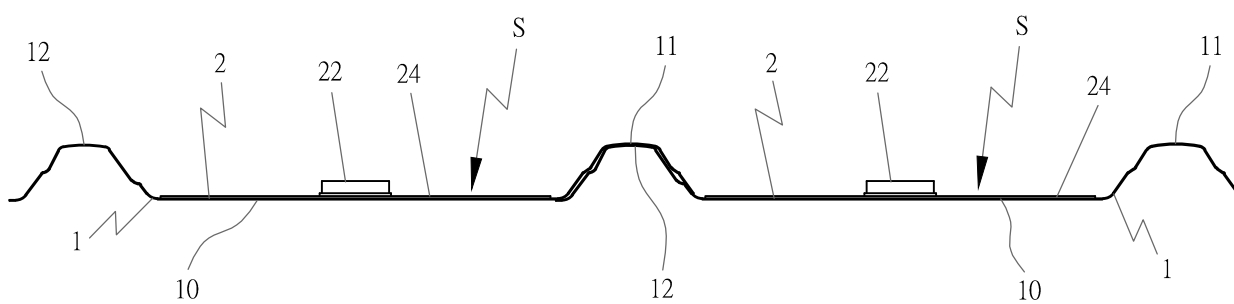


FIG 9A

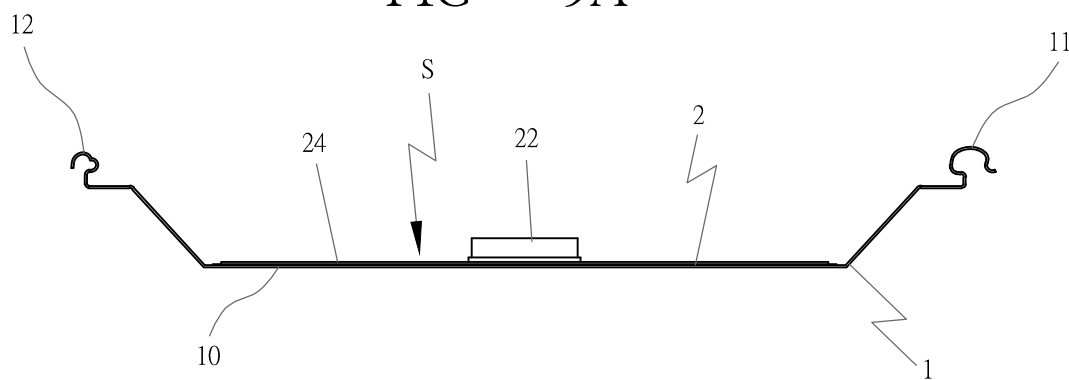


FIG 10

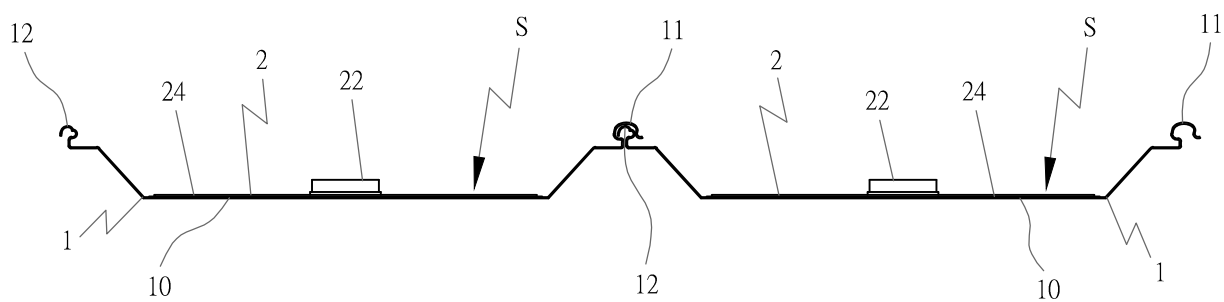


FIG 10A